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Low-power configurable gate with voltage-level translator

Rev. 1 — 19 May 2014

Product data sheet

1. General description

The 74AUP1T98-Q100 provides low-power, low-voltage configurable logic gate functions. Eight patterns of 3-bit input determine the output state. The user can choose the logic functions MUX, AND, OR, NAND, NOR, inverter and buffer. All inputs can be connected to V_{CC} or GND.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 2.3 V to 3.6 V.

The 74AUP1T98-Q100 is designed for logic-level translation applications. The input switching levels accept 1.8 V low-voltage CMOS signals, while operating from either a single 2.5 V or 3.3 V supply voltage.

The wide supply voltage range ensures normal operation as battery voltage drops from 3.6 V to 2.3 V.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

Schmitt trigger inputs make the circuit tolerant to slower input rise and fall times across the entire V_{CC} range.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Wide supply voltage range from 2.3 V to 3.6 V
- High noise immunity
- ESD protection:
 - MIL-STD-883, method 3015 Class 3A. Exceeds 5000 V
 - HBM JESD22-A114F Class 3A. Exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Low static power consumption; I_{CC} = 1.5 μA (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial power-down mode operation

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3. Ordering information

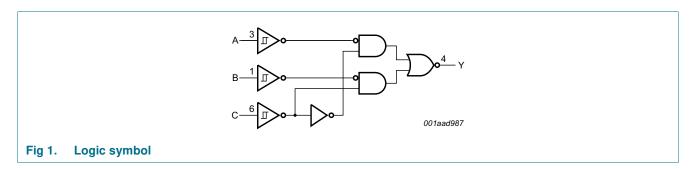
Table 1.Ordering information

Type number	Package					
	Temperature range	Name	Description	Version		
74AUP1T98GW-Q100	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363		

4. Marking

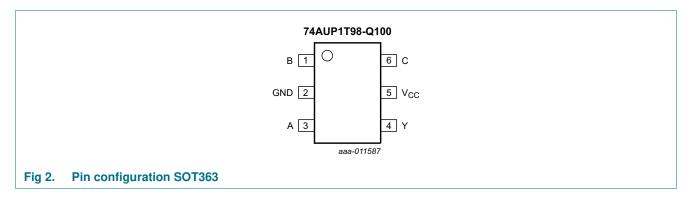
Table 2. Marking Type number Marking code 74AUP1T98GW-Q100 aR

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin des	Table 3. Pin description						
Symbol	Pin	Description					
В	1	data input					
GND	2	ground (0 V)					
A	3	data input					
Y	4	data output					
V _{CC}	5	supply voltage					
С	6	data input					

7. Functional description

Table 4. Function table^[1]

Input	Output		
C	В	Α	Y
L	L	L	Н
L	L	Н	Н
L	Н	L	L
L	Н	Н	L
Н	L	L	Н
Н	L	Н	L
Н	Н	L	Н
Н	Н	Н	L

[1] H = HIGH voltage level; L = LOW voltage level.

7.1 Logic configurations

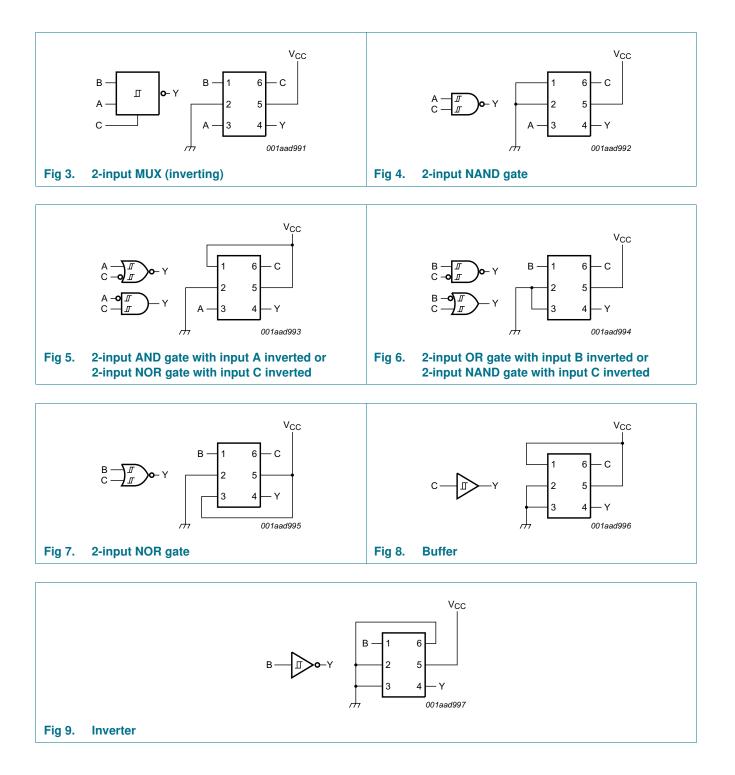
Table 5.Function selection table

Logic function	Figure
2-input MUX (inverting)	see Figure 3
2-input NAND	see Figure 4
2-input NOR with one input inverted	see Figure 5
2-input AND with one input inverted	see Figure 5
2-input NAND with one input inverted	see Figure 6
2-input OR with one input inverted	see Figure 6
2-input NOR	see Figure 7
Buffer	see Figure 8
Inverter	see Figure 9

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74AUP1T98-Q100

Low-power configurable gate with voltage-level translator



8. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage	1	1 -0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	1 -0.5	+4.6	V
lo	output current	$V_{O} = 0 V \text{ to } V_{CC}$	-	±20	mA
I _{CC}	supply current		-	+50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \text{ °C to } +125 \text{ °C}$	2] -	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SC-88 package: above 87.5 $^\circ\text{C}$ the value of P_tot derates linearly with 4.0 mW/K.

9. Recommended operating conditions

Table 7. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		2.3	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V _{CC}	V
		Power-down mode; $V_{CC} = 0 V$	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C

10. Static characteristics

Table 8. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit		
T _{amb} = 2	5 ℃							
V _{T+}	positive-going threshold	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	0.60	-	1.10	V		
voltage		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	0.75	-	1.16	V		
V _{T-} neg	negative-going threshold	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	0.35	-	0.60	V		
voltage		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	0.50	-	0.85	V		
V _H	hysteresis voltage	$(V_{H} = V_{T+} - V_{T-})$			I	I		
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	0.23	-	0.60	V		
		V _{CC} = 3.0 V to 3.6 V	0.25	-	0.56	V		
V _{OH}	HIGH-level output voltage	$V_{I} = V_{T+}$ or V_{T-}						
		I_{O} = -20 μ A; V_{CC} = 2.3 V to 3.6 V	$V_{CC}-0.1$	-	-	V		
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V		
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V		
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V		
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V		
V _{OL}	LOW-level output voltage	$V_{I} = V_{T+}$ or V_{T-}						
		I_{O} = 20 μ A; V_{CC} = 2.3 V to 3.6 V	-	-	0.10	V		
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V		
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V		
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.31	V		
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.44	V		
lı –	input leakage current	$V_{I} = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μA		
I _{OFF}	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.1	μA		
ΔI_{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.2	μA		
I _{CC}	supply current	$V_1 = GND \text{ or } V_{CC}; I_0 = 0 \text{ A};$ $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$	-	-	1.2	μA		
Cı	input capacitance	$V_{CC} = 0$ V to 3.6 V; $V_I = GND$ or V_{CC}	-	0.8	-	pF		
Co	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	1.7	-	pF		
T _{amb} = –	40 °C to +85 °C							
V _{T+}	positive-going threshold	$V_{CC} = 2.3 \text{ V} \text{ to } 2.7 \text{ V}$	0.60	-	1.10	V		
	voltage	V _{CC} = 3.0 V to 3.6 V	0.75	-	1.19	V		
V _{T-}	negative-going threshold	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	0.35	-	0.60	V		
	voltage	V _{CC} = 3.0 V to 3.6 V	0.50	-	0.85	V		
V _H	hysteresis voltage	$(V_{H} = V_{T_{+}} - V_{T_{-}})$			I	I		
	_	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	0.10	-	0.60	V		
		V _{CC} = 3.0 V to 3.6 V	0.15	-	0.56	V		

Low-power configurable gate with voltage-level translator

Table 8. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OH}	HIGH-level output voltage	$V_{I} = V_{T+}$ or V_{T-}				
		I_O = –20 $\mu\text{A};V_{CC}$ = 2.3 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{T+} \text{ or } V_{T-}$				
		I_{O} = 20 µA; V_{CC} = 2.3 V to 3.6 V	-	-	0.1	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.33	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.33	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.45	V
lı	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μA
OFF	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.5	μA
ΔI_{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.5	μA
lcc	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$	-	-	1.5	μA
∆l _{CC}	additional supply current		-	-	4	μA
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V; } I_{O} = 0 \text{ A}$	-	-	12	μA
$T_{amb} = -4$	40 °C to +125 °C					
V _{T+}	positive-going threshold	V _{CC} = 2.3 V to 2.7 V	0.60	-	1.10	V
	voltage	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	0.75	-	1.19	V
V _{T-}	negative-going threshold	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	0.33	-	0.64	V
	voltage	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	0.46	-	0.85	V
V _H	hysteresis voltage	$(V_{H} = V_{T_{+}} - V_{T_{-}})$				
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	0.10	-	0.60	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	0.15	-	0.56	V
V _{OH}	HIGH-level output voltage	$V_{I} = V_{T+}$ or V_{T-}				
		$I_{O} = -20 \ \mu\text{A}; \ V_{CC} = 2.3 \ \text{V} \text{ to } 3.6 \ \text{V}$	V _{CC} - 0.11	-	-	V
		$I_{\rm O} = -2.3 \text{ mA}; V_{\rm CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_{\rm O} = -3.1 \text{ mA}; V_{\rm CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{\rm O} = -2.7 \text{ mA}; V_{\rm CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{\rm O} = -4.0 \text{ mA}; V_{\rm CC} = 3.0 \text{ V}$	2.30	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{T+}$ or V_{T-}				
0L		$I_{O} = 20 \ \mu\text{A}; V_{CC} = 2.3 \ \text{V} \text{ to } 3.6 \ \text{V}$	-	-	0.11	V
		$I_0 = 2.3 \text{ mA; } V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_0 = 3.1 \text{ mA; } V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
l _l	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$			±0.75	μA

74AUP1T98-Q100

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Low-power configurable gate with voltage-level translator

At recommended operating conditions; voltages are referenced to GND (ground = $0 V$).								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
I _{OFF}	power-off leakage current	V_1 or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V		-	-	±0.75	μA	
ΔI_{OFF}	additional power-off leakage current			-	-	±0.75	μA	
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \; A; \\ V_{CC} = 2.3 \; V \; to \; 3.6 \; V \end{array}$		-	-	3.5	μA	
ΔI_{CC}	additional supply current	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}; I_{O} = 0 \text{ A}$	[1]	-	-	7	μA	
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}; I_O = 0 \text{ A}$	[2]	-	-	22	μA	

Table 8. Static characteristics ... continued

[1] One input at 0.3 V or 1.1 V, other input at $V_{CC} \mbox{ or GND}.$

[2] One input at 0.45 V or 1.2 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Dynamic characteristics Table 9.

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 11.

Symbol	Parameter	Conditions	25 °C			-4	0 °C to +1	25 °C	Unit
			Min	Typ <mark>[1]</mark>	Max	Min	Max (85 °C)	Max (125 °C)	
$V_{\rm CC} = 2.3$	3 V to 2.7 V; V _I = 1.6	55 V to 1.95 V					·		
t _{pd}	propagation delay	A, B, C to Y; see Figure 10 [2]							
		C _L = 5 pF	2.0	3.6	5.7	0.5	6.8	7.5	ns
		C _L = 10 pF	2.5	4.2	6.3	1.0	7.9	8.7	ns
		C _L = 15 pF	2.9	4.6	6.9	1.0	8.7	9.6	ns
		C _L = 30 pF	3.9	5.8	8.3	1.5	10.8	11.9	ns
$V_{\rm CC} = 2.3$	3 V to 2.7 V; V _I = 2.3	3 V to 2.7 V							
t _{pd}	propagation delay	A, B, C to Y; see Figure 10 [2]							
		$C_L = 5 \text{ pF}$	1.7	3.4	5.6	0.5	6.0	6.6	ns
		C _L = 10 pF	2.1	4.0	6.3	1.0	7.1	7.9	ns
		C _L = 15 pF	2.5	4.5	6.9	1.0	7.9	8.7	ns
		C _L = 30 pF	3.4	5.6	8.4	1.5	10.0	11.0	ns
$V_{\rm CC} = 2.3$	3 V to 2.7 V; V _I = 3.0) V to 3.6 V							-
t _{pd}	propagation delay	A, B, C to Y; see Figure 10 [2]							
		$C_L = 5 \text{ pF}$	1.3	3.2	5.2	0.5	5.5	6.1	ns
		C _L = 10 pF	1.8	3.7	5.9	1.0	6.5	7.2	ns
		C _L = 15 pF	2.2	4.2	6.5	1.0	7.4	8.2	ns
		C _L = 30 pF	3.1	5.4	7.9	1.5	9.5	10.5	ns
$V_{\rm CC} = 3.0$	0 V to 3.6 V; V _I = 1.6	55 V to 1.95 V							-
t _{pd}	propagation delay	A, B, C to Y; see <u>Figure 10</u> [2]							
		C _L = 5 pF	2.0	2.9	4.1	0.5	8.0	8.8	ns
		C _L = 10 pF	2.4	3.5	4.8	1.0	8.5	9.4	ns
		C _L = 15 pF	2.8	3.9	5.4	1.0	9.1	10.1	ns
		C _L = 30 pF	3.6	5.1	6.9	1.5	9.8	10.8	ns

74AUP1T98-Q100

Low-power configurable gate with voltage-level translator

25 °C –40 °C to +125 °C Symbol Parameter Conditions Unit Min Typ^[1] Max Min Max Max (85 °C) (125 °C) $V_{CC} = 3.0 \text{ V}$ to 3.6 V; $V_{I} = 2.3 \text{ V}$ to 2.7 V propagation delay A, B, C to Y; see Figure 10 [2] t_{pd} $C_1 = 5 pF$ 1.5 2.8 4.4 0.5 5.3 5.9 ns $C_L = 10 \text{ pF}$ 2.0 3.4 5.1 1.0 6.1 6.8 ns $C_{1} = 15 \, pF$ 2.4 3.9 5.7 1.0 7.5 6.8 ns $C_{I} = 30 \text{ pF}$ 3.4 5.0 7.2 1.5 8.5 9.4 ns $V_{CC} = 3.0 V$ to 3.6 V; $V_1 = 3.0 V$ to 3.6 V propagation delay A, B, C to Y; see Figure 10 [2] t_{pd} $C_1 = 5 pF$ 4.4 4.7 1.3 2.8 0.5 5.2 ns $C_{I} = 10 \, pF$ 1.7 3.3 5.2 1.0 5.7 6.3 ns $C_{I} = 15 \, pF$ 2.1 3.8 5.8 1.0 6.2 6.9 ns $C_L = 30 \text{ pF}$ 3.1 5.0 7.2 1.5 7.8 8.6 ns T_{amb} = 25 °C $f_i = 1 \text{ MHz}; V_i = \text{GND to } V_{CC}$ [3] CPD power dissipation capacitance V_{CC} = 2.3 V to 2.7 V 3.6 pF _ ---- $V_{CC} = 3.0 V$ to 3.6 V 4.3 pF _ _ _ _ _

Table 9. Dynamic characteristics ... continued

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 11.

[1] All typical values are measured at nominal V_{CC}.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

f_i = input frequency in MHz;

fo = output frequency in MHz;

 C_{I} = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$ = sum of the outputs.

Low-power configurable gate with voltage-level translator

12. Waveforms

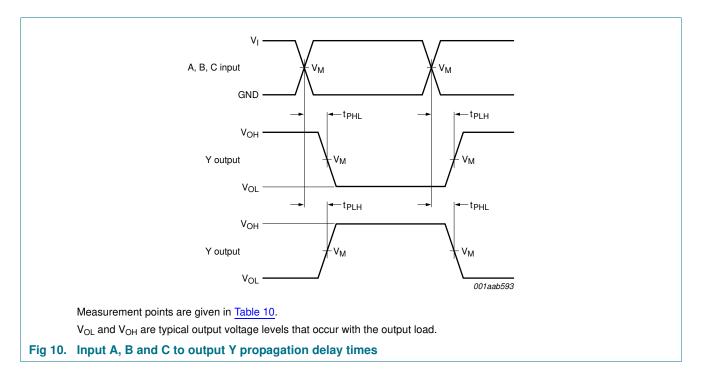


Table 10. Measurement points

Supply voltage	Output	Input				
V _{cc}	V _M	V _M	VI	$t_r = t_f$		
2.3 V to 3.6 V	$0.5 imes V_{CC}$	$0.5 imes V_I$	1.65 V to 3.6 V	≤ 3.0 ns		

Low-power configurable gate with voltage-level translator

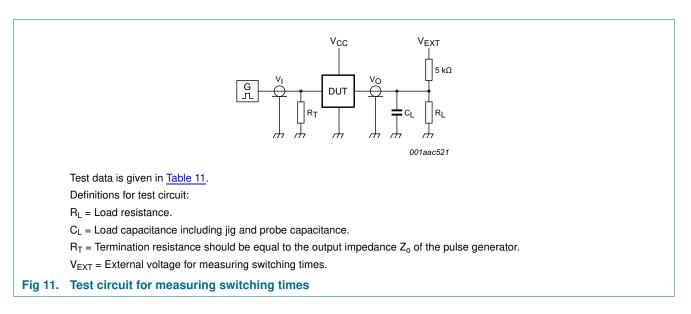


Table 11. Test data

Supply voltage	Load	V _{EXT}			
V _{cc}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
2.3 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times, $R_L = 5 \text{ k}\Omega$. For measuring propagation delays, setup and hold times, and pulse width, $R_L = 1 \text{ M}\Omega$.

Low-power configurable gate with voltage-level translator

13. Package outline

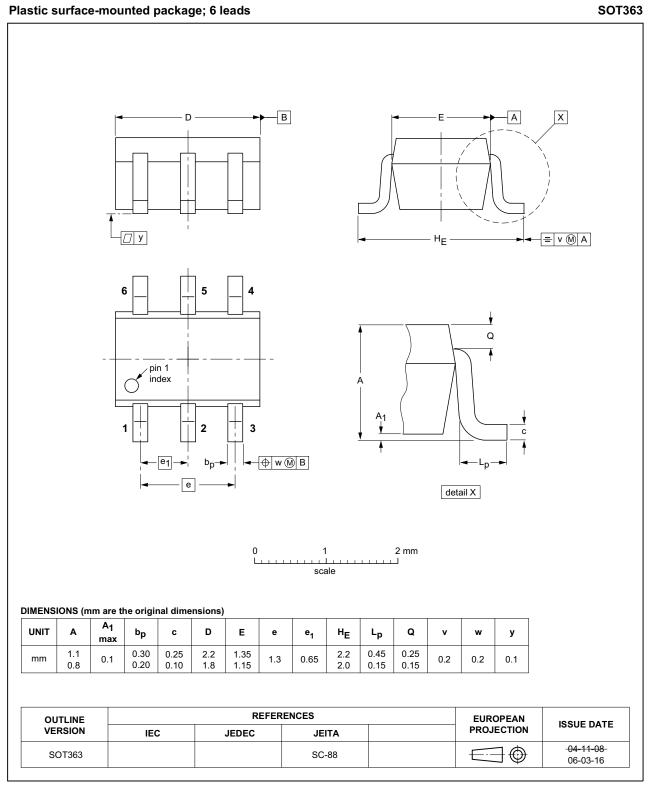


Fig 12. Package outline SOT363 (SC-88)

ormation	provided	in this	document	is	subject	to	legal	disclaimer	s.

74AUP1T98-Q100

All info

14. Abbreviations

Table 12. Abbreviations				
Description				
Charged Device Model				
Complementary Metal-Oxide Semiconductor				
Device Under Test				
ElectroStatic Discharge				
Human Body Model				
Military				
Machine Model				

15. Revision history

Table 13.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1T98_Q100 v.1	20140519	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Low-power configurable gate with voltage-level translator

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Nexperia

74AUP1T98-Q100

Low-power configurable gate with voltage-level translator

18. Contents

1	General description 1
2	Features and benefits 1
3	Ordering information 2
4	Marking 2
5	Functional diagram 2
6	Pinning information 2
6.1	Pinning 2
6.2	Pin description 3
7	Functional description 3
7.1	Logic configurations 3
8	Limiting values 5
9	Recommended operating conditions 5
10	Static characteristics 6
11	Dynamic characteristics 8
12	Waveforms
13	Package outline 12
14	Abbreviations 13
15	Revision history 13
16	Legal information 14
16.1	Data sheet status 14
16.2	Definitions 14
16.3	Disclaimers
16.4	Trademarks 15
17	Contact information 15
18	Contents 16